

WHAT IS CLAIMED IS:

1. A method for manufacturing a group III nitride compound semiconductor device, comprising a step of:

irradiating a surface of a wafer with ultraviolet rays
5 to thereby clean said surface of said wafer.

2. A method for manufacturing a group III nitride compound semiconductor device according to claim 1, wherein said ultraviolet rays have a central wavelength of 172 nm.

3. A method for manufacturing a group III nitride compound semiconductor device according to claim 1, wherein said ultraviolet rays are emitted from an excimer lamp.

4. A method for manufacturing a group III nitride compound semiconductor device according to claim 1, wherein said cleaning step is carried out on a p-type semiconductor layer.

5. A method for cleaning a group III nitride compound semiconductor device having an electrode on a p-type group III nitride compound semiconductor layer, comprising a step of:

irradiating said group III nitride compound semiconductor device with ultraviolet rays before and/or after said electrode

are formed.

6. A cleaning method according to claim 5, wherein said ultraviolet rays have a central wavelength of 172 nm.

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7. A cleaning method according to claim 5, wherein said ultraviolet rays are emitted from an excimer lamp.

8. A method for cleaning a group III nitride compound semiconductor device cut out of a wafer, comprising a step of:
irradiating said group III nitride compound semiconductor device with ultraviolet rays to thereby clean said group III nitride compound semiconductor device.

9. A cleaning method according to claim 8, wherein said ultraviolet rays have a central wavelength of 172 nm.

10. A cleaning method according to claim 8, wherein said ultraviolet rays are emitted from an excimer lamp.

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